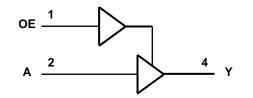


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Pin NO.	Description
OE	1	Output Enable
A	2	Data Input
GND	3	Ground
Y	4	Data Output
V _{CC}	5	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
OE	А	Y
Н	Н	Н
Н	L	L
L	Х	Z



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-20	mA
I _{OK}	Output Clamp Current (V _O < 0 or V _O > V _{CC})	±20	mA
Ι _Ο	Continuous output current ($V_0 = 0$ to V_{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	I _{GND} Continuous current through GND		mA
ΤJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		2	5.5	V
		$V_{CC} = 2V$	1.5		
VIH	High-level Input Voltage	$V_{CC} = 3V$	2.1		V
		$V_{CC} = 5.5V$	3.85		
		$V_{CC} = 2V$		0.5	
VIL	Low-level input voltage	$V_{CC} = 3V$		0.9	V
		$V_{CC} = 5.5 V$		1.65	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 2V$		-50	uA
I _{OH}	High-level output current	$V_{CC} = 3.3V \pm 0.3V$		-4	mA
		$V_{CC} = 5V \pm 0.5V$		-8	IIIA
		$V_{CC} = 2V$		50	uA
I _{OL}	Low-level output current	$V_{CC} = 5V \pm 0.5V$		4	mA
		$V_{CC} = 3V$		8	IIIA
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3V \pm 0.3V$		100	ns/V
ΔυΔν	rate	$V_{CC} = 5V \pm 0.5V$		20	115/ V
T _A	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at $V_{\mbox{CC}}$ or Ground.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Electrical Characteristics

O week at	Demonster	Tast Oan ditions	N		25⁰C		-40°C 1	o 85⁰C	-40°C t	o 125⁰C	11	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Min	Max	Min	Max	Unit	
			2V	1.9	2		1.9		1.9			
	High Level	Ι _{ΟΗ} = -50μΑ	3V	2.9	3		2.9		2.9			
V _{OH}	Output	Output		4.5V	4.4	4.5		4.4		4.4		V
	Voltage	I _{OH} = -4mA	3V	2.58			2.48		2.40			
		I _{OH} = -8mA	4.5V	3.94			3.8		3.70			
			2V			0.1		0.1		0.1		
	Low Level	I _{OL} = 50μA	3V			0.1		0.1		0.1		
V _{OL}	Output		4.5V			0.1		0.1		0.1	V	
	Voltage	$I_{OL} = 4mA$	3V			0.36		0.44		0.55		
		$I_{OL} = 8mA$	4.5V			0.36		0.44		0.55		
lı –	Input Current	$V_1 = 5.5 V \text{ or GND}$	0 to 5.5V			± 0.1		± 1		±2	μA	
I _{OZ}	Z State Leakage Current	V_{O} =0 to 5.5 V	5.5V			0.25		2.5		10	μA	
I _{CC}	Supply Current	V _I = 5.5V or GND I _O =0	5.5V			1		10		40	μA	
CI	Input Capacitance	$V_I = V_{CC} - or GND$	5.5V		2.0	10		10		10	pF	
Α	Thermal Resistance	SOT25	(Note 4)		195						°C/W	
θ_{JA}	Junction-to- Ambient	SOT353	(NOLE 4)		430						0/00	
A.,	Thermal Resistance	SOT25	(Note 4)		58						°C/W	
θ _{JC}	Junction-to- Case	SOT353	(Note 4)		155						C/VV	

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout

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SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

V_{CC} = 3.3V ± 0.3 (see Figure 1)

Parameter	From	то			25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	Unit
Parameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	А	V	C _L =15pF	0.6	4.4	8.0	0.6	9.5	0.6	10.0	ns
t _{pd}	A	ř	C _L =50pF	0.6	6.3	11.5	0.6	13.0	0.6	14.5	ns
		v	C _L =15pF	0.6	4.9	8.0	0.6	9.5	0.6	10.0	ns
t _{en}	OE	Ŷ	C _L =50pF	0.6	7.0	11.5	0.6	13.0	0.6	14.5	ns
		v	C _L =15pF	0.6	6.3	9.7	0.6	11.5	0.6	12.5	ns
t _{dis}	OE	ŕ	C _L =50pF	0.6	9.0	13.2	0.6	15.0	0.6	16.5	ns

$V_{CC} = 5V \pm 0.5V$ (see Figure 1)

Deremeter	From	то			25⁰C		-40 ºC t	o 85 ⁰C	-40 ºC to	o 125 ⁰C	Unit
Parameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	А	V	C _L =15pF	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns
t _{pd}	A	ř	C _L =50pF	0.6	4.7	7.5	0.6	8.5	0.6	9.5	ns
	OE	V	C _L =15pF	0.6	3.6	5.6	0.6	6.3	0.6	7.0	ns
t _{en}	UE	ř	C _L =50pF	0.6	5.4	8.0	0.6	9.0	0.6	9.5	ns
	OE		C _L =15pF	0.6	4.3	6.8	0.6	8.0	0.6	8.5	ns
t _{dis}	UE	ř	C _L =50pF	0.6	6.1	8.8	0.6	10.0	0.6	11.0	ns

Operating Characteristics

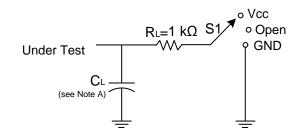
T_A = 25 °C

	Parameter	Test Conditions	V _{CC} = 5 V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 1 MHz No Load	12	pF



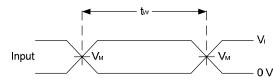
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

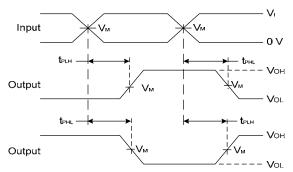


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

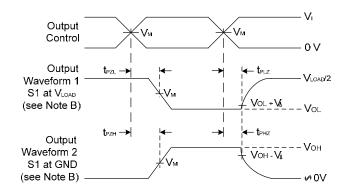
N	In	puts	V	C	V۵
V _{CC}	VI	t _r /t _f	V _M	CL	VΔ
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

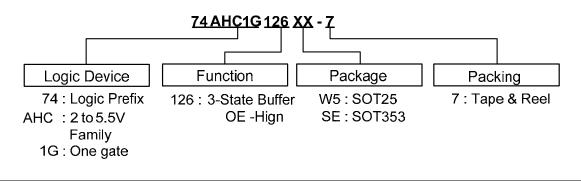
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 1 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as $t_{\text{dis.}}$
- E. t_{PZL} and t_{PZH} are the same as $t_{\text{EN.}}$
- F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

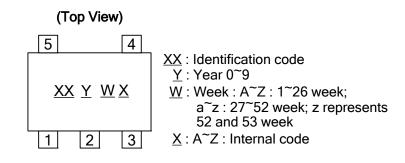
Ordering Information



	Device	Package Packaging		7" Tape a	and Reel
	Device	Code	(Note 5)	Quantity	Part Number Suffix
Pb ,	74AHC1G126W5-7	W5	SOT25	3000/Tape & Reel	-7
B ,	74AHC1G126SE-7	SE	SOT353	3000/Tape & Reel	-7

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



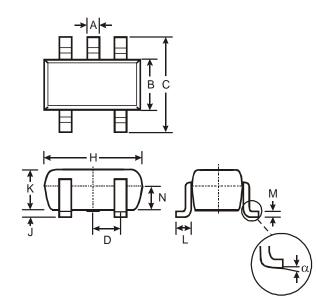
Part Number	Package	Identification Code
74AHC1G126W5	SOT25	ΥZ
74AHC1G126SE	SOT353	ΥZ



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

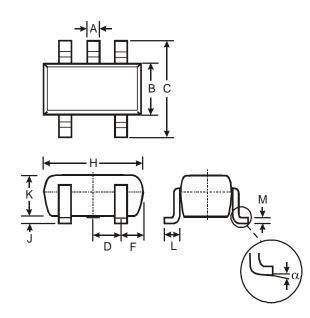
(1) Package Type: SOT25



SOT25				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
в	1.50	1.70	1.60	
С	2.70	3.00	2.80	
D		_	0.95	
Н	2.90	3.10	3.00	
ر	0.013	0.10	0.05	
K	1.00	1.30	1.10	
┙	0.35	0.55	0.40	
Μ	0.10	0.20	0.15	
Ν	0.70	0.80	0.75	
α	0°	8°		
All Dimensions in mm				

(2) Package Type: SOT353

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SOT353				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
κ	0.90	1.00		
L	0.25	0.40		
Μ	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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